ABSTRACT

BACK GATE CONTACT FOR SILICON ON INSULATOR TECHNOLOGY

A process for creating a back gate contact, in an SOI layer, that can easily be incorporated into a MOSFET fabrication recipe, has been developed. The back gate contact consists of a etched trench, lined with insulator, and filled with doped polysilicon. The polysilicon filled trench electrically connects the semiconductor substrate to overlying metal contacts.

(FIGURE 1 IS SUGGESTED FOR PUBLICATION)